MITSUBISHI SEMICONDUCTOR < GaAs FET>

MGFS48B2122

2.11 - 2.17 GHz BAND 60W GaAs FET

20.4±0.2

DESCRIPTION

The MGFS48B2122 is a 60W push-pull type GaAs Power FET especially designed for use in 2.11 - 2.17GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

- Push-pull configuration
- High output power

Pout = 60W (TYP.) @ f=2.17 GHz

- High power gain GLP = 12 dB (TYP.) @ f=2.17GHz
- High power added efficiency P.A.E. = 48 % (TYP.) @ f=2.17GHz

APPLICATION

2.11-2.17GHz band power amplifier for W-CDMA Base Station

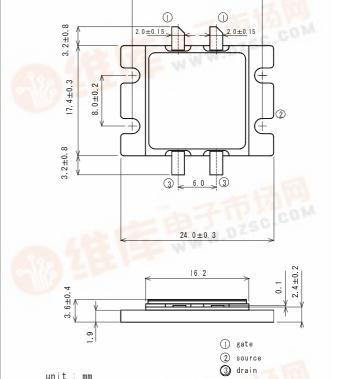
QUALITY GRADE

RECOMMENDED BIAS CONDITIONS

VDS = 12(V)ID = 2.0 (A)RG=20 (ohm) for each gate

GF-47

OUTLINE



ABSOLUTE MAXIMUM RATINGS (Ta=25deg.C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain voltage	-20	V
VGSO	Gate to source voltage	-10	V
PT *1	Total power dissipation	125	W
Tch	Channel temperature	175	deg.C
Tstg	Storage temperature	-65 / +175	deg.C

^{*1:} Tc=25deg.C

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ELECTRICAL CHARACTERISTICS (Ta=25deg.C)

Symbol	Parameter	Test conditions		Limits			Unit
	wIT			Min.	Тур.	Max.	
GLP	Linear power gain	Pin=22dBm		11	12	-	dB
Pout	Output power		VDS=12V, ID(RF off)=2.0A	47	48	-	dBm
ID(RF)	Drain current	Pin=39dBm	f=2.17GHz	-	11	15	А
P.A.E.	Power added efficiency			-	48	-	%
Rth (ch-d)	Thermal resistance	Channel to Case		-	1	1.2	deg.C/W

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